ICMOVPE XXII July 12-17, 2026 ICC JEJU, Jeju Island, Korea

Session Title:	**[MoA2] Advanced Growth Techniques - I**
Session Date:	**July 13 (Mon.), 2026**
Session Time:	**14:00-15:45**
Session Room:	**Room A (Baekrok Hall B-1, 1F)**
Session Chairs	

[MoA2-1] [Invited] **14:00-14:30**

Remote Epitaxy of Deformable and Stacktronic Devices

Young Joon Hong, Sungkyunkwan University, Korea

[MoA2-2] **14:30-14:45**

Fabrication of Wafer-Scale Freestanding GaN Membrane Utilizing Transfer-Free Thin Amorphous Carban Layer via MOCVD-Based Remote Epitaxy

Joonghoon Choi, Wonkwang Yang, Chang Soo Kim, Junhyun Bae, and Young Joon Hong, Sungkyunkwan University, Korea

[MoA2-3] **14:45-15:00**

Remote Epitaxy of α-Ga_2O_3 via Polycrystalline MoS_2

Gyeong Ryul Lee and Roy. B. Chung, Kyungpook National University, Korea

[MoA2-4] **15:00-15:15**

MOCVD of GaN and AlGaN/GaN Heterostructures on Si(001) by Wafer-Scale MoS_2 Templates

Seung Hoon Lee[1], Chen Chen[1], Brian M. Bersch[2], and Joan M. Redwing[1], [1] Pennsylvania State University, USA, [2] Northrop Grumman Mission Systems, USA

[MoA2-5] **15:15-15:30**

InGaN Quantum Wells Grown on Spatially Patterned Substrates – Towards the 3D Laser Emitters

Grzanka Ewa, Grzanka Szymon, Robert Czernecki, Mikolaj Grabowski, Roman Hrytsak, Artur Lachowski, Julita Smalc-Koziorowska, and Michal Leszczynski, Institute of High Pressure Physics, Poland

[MoA2-6] **15:30-15:45**

Room-Temperature Continuous-Wave III–V/Si PhC Lasers on SOI Using Selective Lateral Heteroepitaxy

Xingyu Yang, Yao Chen, Jinglong Chen, Siyuan Yu, and Yu Han, Sun Yat-sen University, China